

2D Valley-Spin Transport in Transition Metal Dichalcogenides

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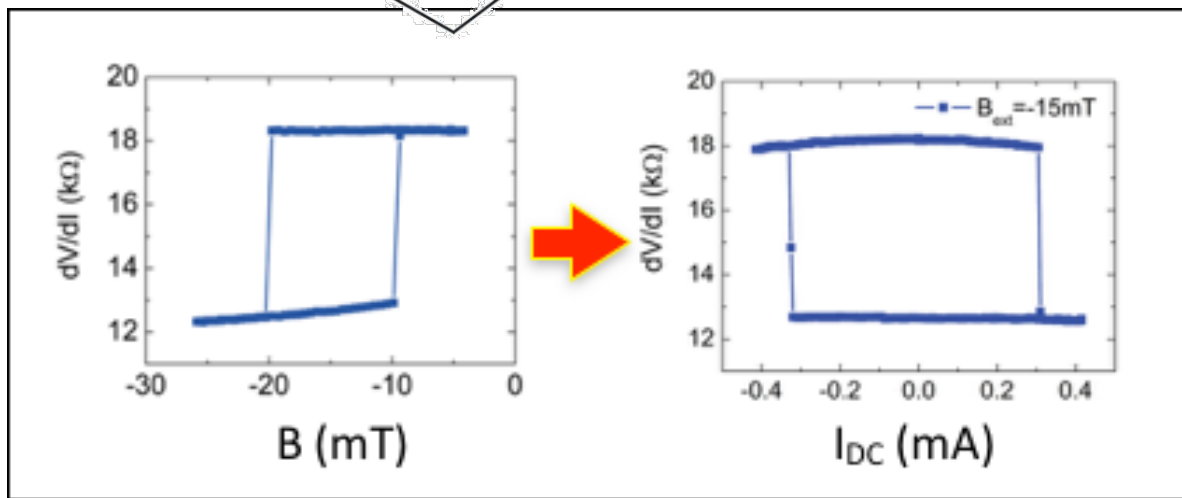
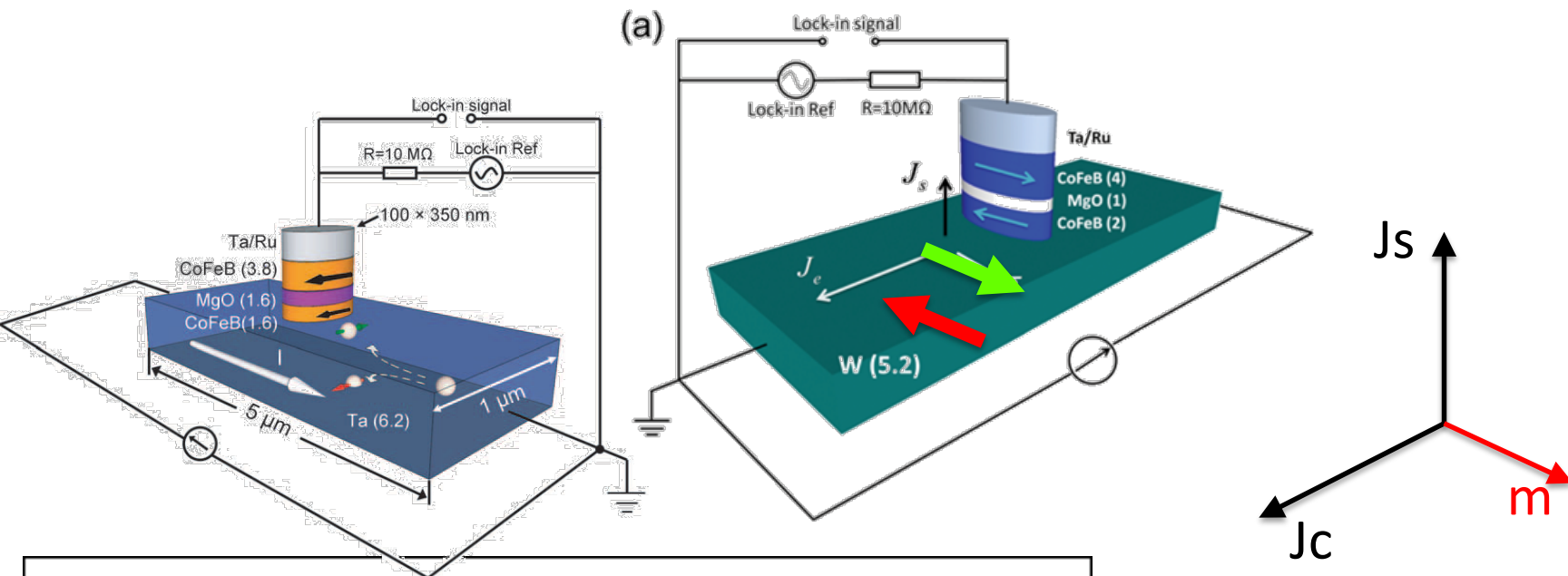
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Spintronics Workshop
September 11, 2019

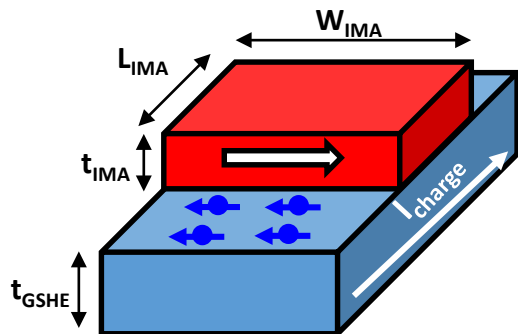
Spin Hall Effect



Liu et al., *Science* **336**, 555 (2012)
 Pai et al., *APL* **101**, 122404 (2012)
 Liu et al., *PRL* **109**, 096602 (2012)

Switching Current of SOT Switching Based Write Unit

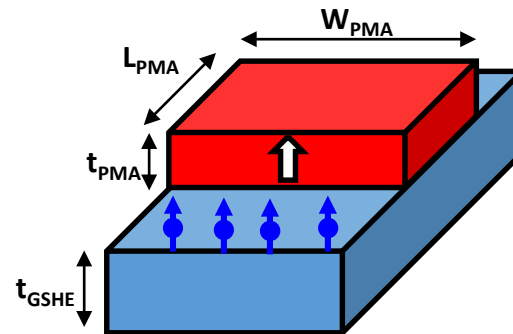
IMA on in-plane GSHE



$$J_{C,WRITE} = \frac{2e}{\hbar} \mu_0 M_S H_K t \alpha \left(1 + \frac{H_D}{H_K} \right) \frac{1}{\theta_{SH}}$$

IMA switched by in-plane GSHE

PMA on out-of-plane GSHE

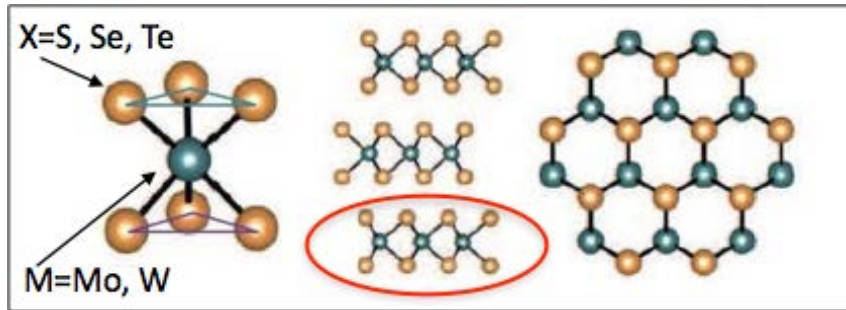


$$J_{C,WRITE} = \frac{2e}{\hbar} \mu_0 M_S H_K t \alpha \frac{1}{\theta_{SH}}$$

PMA switched by out-of-plane GSHE

Switching Energy

Transition Metal Dichalcogenides (2H – MX₂)



Bulk → Monolayer: D_{6h} → D_{3h}
Loss of inversion symmetry

Time reversal symmetry + ~~Inversion symmetry~~

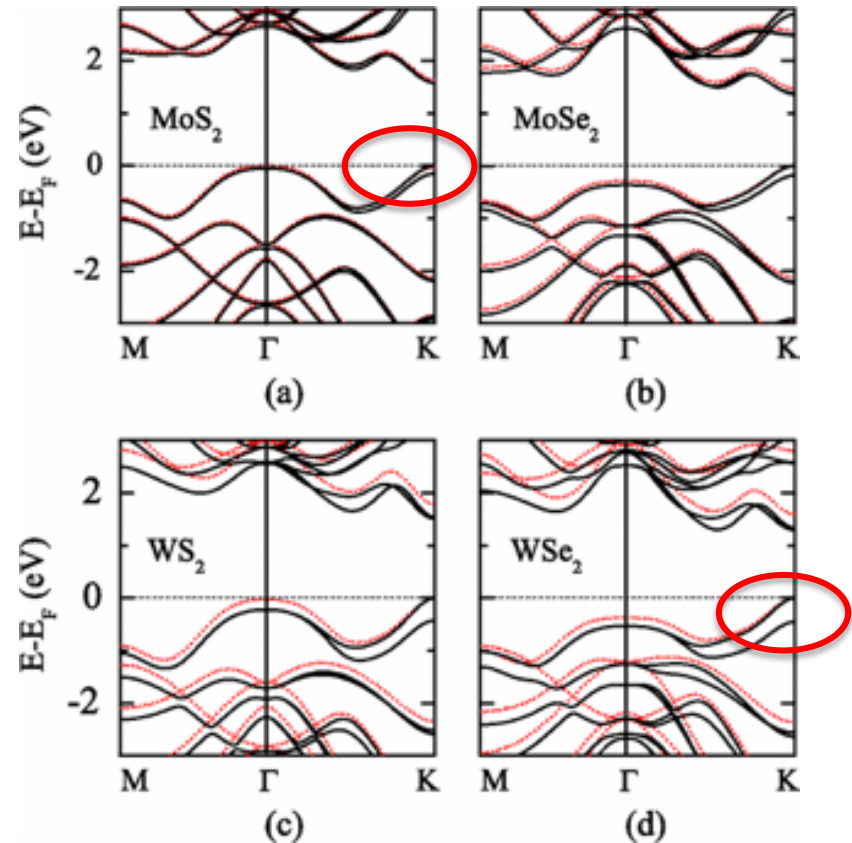
$$E^\uparrow(\vec{k}) = E^\downarrow(-\vec{k}) \quad \text{and} \quad \cancel{E^\uparrow(\vec{k}) = E^\uparrow(-\vec{k})}$$



~~Kramer's degeneracy~~

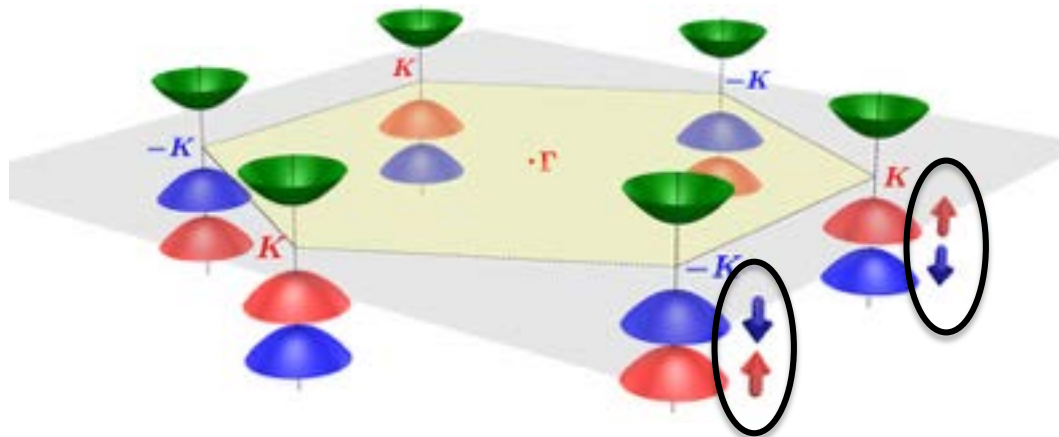
$$\cancel{E^\uparrow(\vec{k}) = E^\downarrow(\vec{k})}$$

- Spin orbit interaction **breaks the spin degeneracy** in monolayer TMD.
- **Spin polarization is out-of-plane** due to in-plane electron motion and in-plane potential gradient asymmetry



Z. Y. Zhu, et al., PRB **84**, 153402 (2011)

Valley Dependent Spin Splitting in TMDs



D. Xiao, et al., PRL **108**, 196802 (2012)

Berry curvature:

$$\Omega(\vec{k}) = \nabla_{\vec{k}} \times \langle u_n(\vec{k}) | i \nabla_{\vec{k}} | u_n(\vec{k}) \rangle$$

Analogous to: $\vec{B} = \nabla \times \vec{A}$

Broken inversion symmetry:

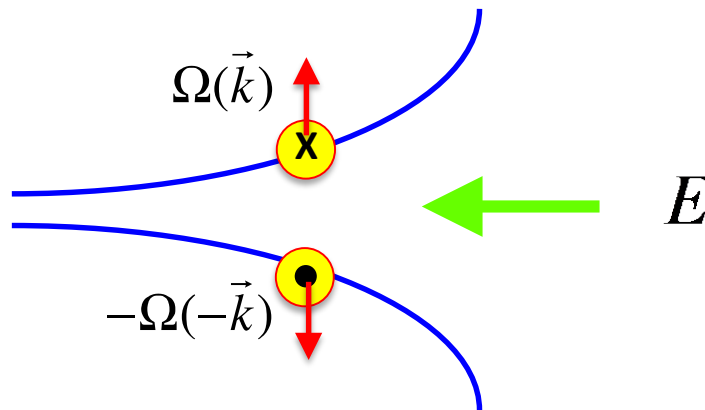
$$\Omega(\vec{k}) \neq 0$$

Valley Spin Hall effect $\hbar \vec{v} = \nabla_{\vec{k}} \varepsilon_n(\vec{k}) - e \vec{E} \times \vec{\Omega}$

Time reversal symmetry:

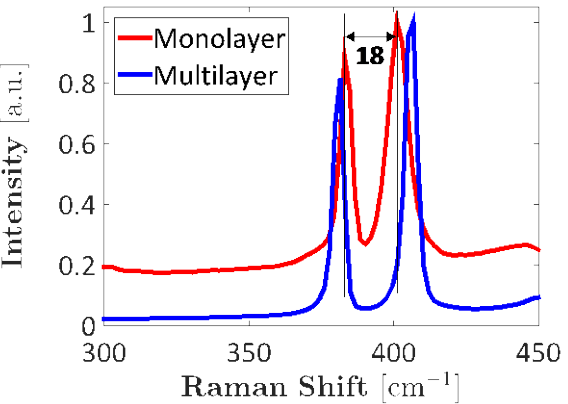
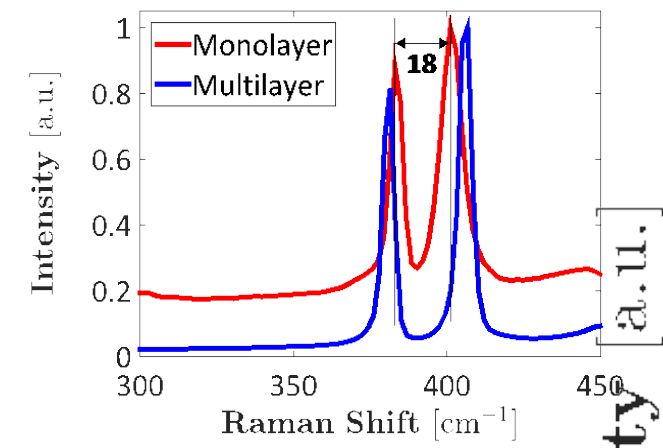
$$\Omega(\vec{k}) = -\Omega(-\vec{k})$$

$$E^\uparrow(\vec{k}) = E^\downarrow(-\vec{k})$$



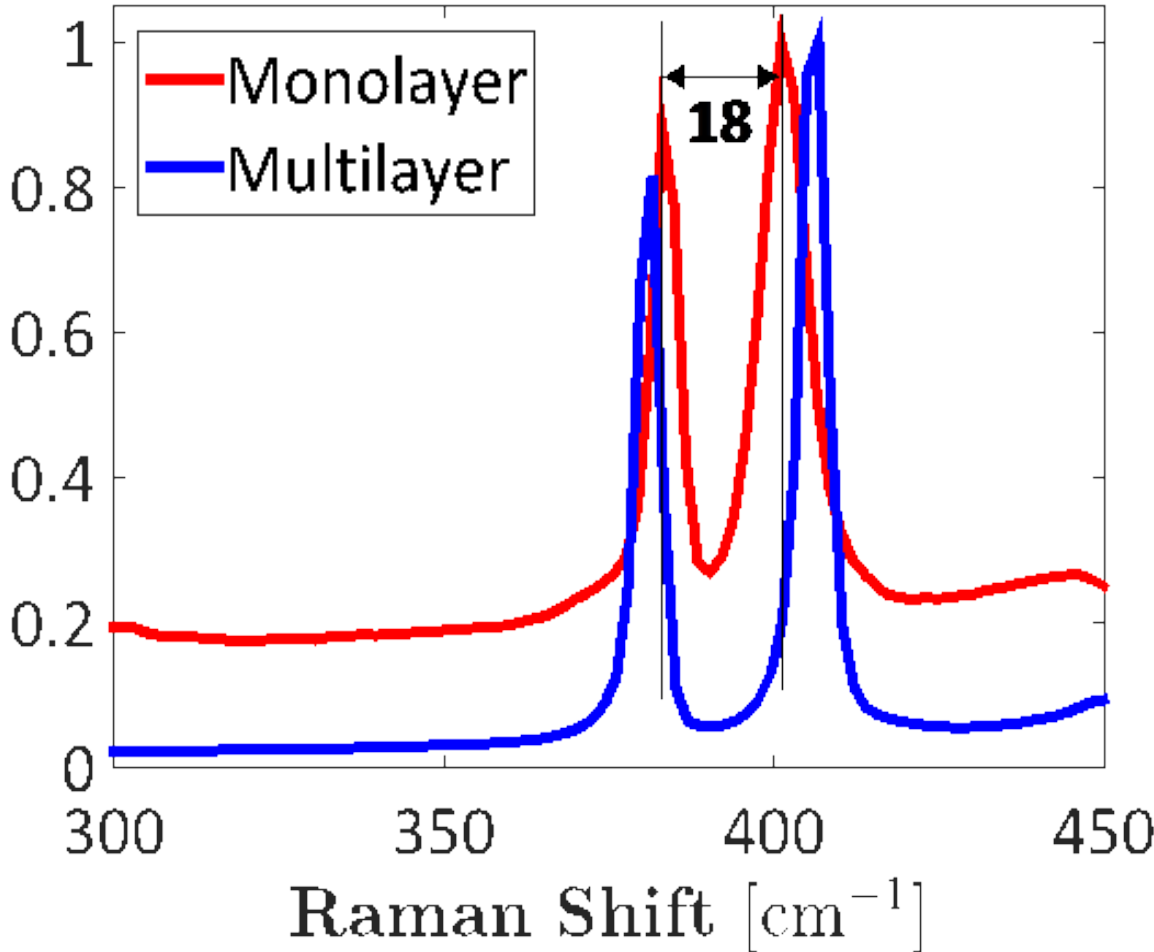
K and -K valleys with opposite Berry curvature develop **anomalous velocities with opposite directions!**

Monolayer and Multilayer MoS₂ Characterization



Transfer Characteristics

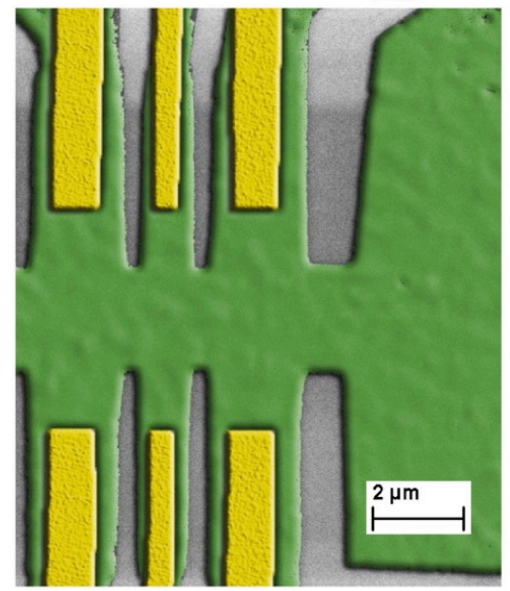
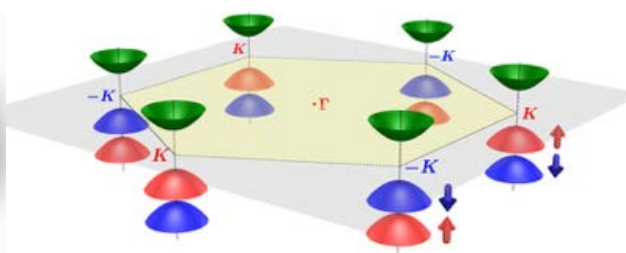
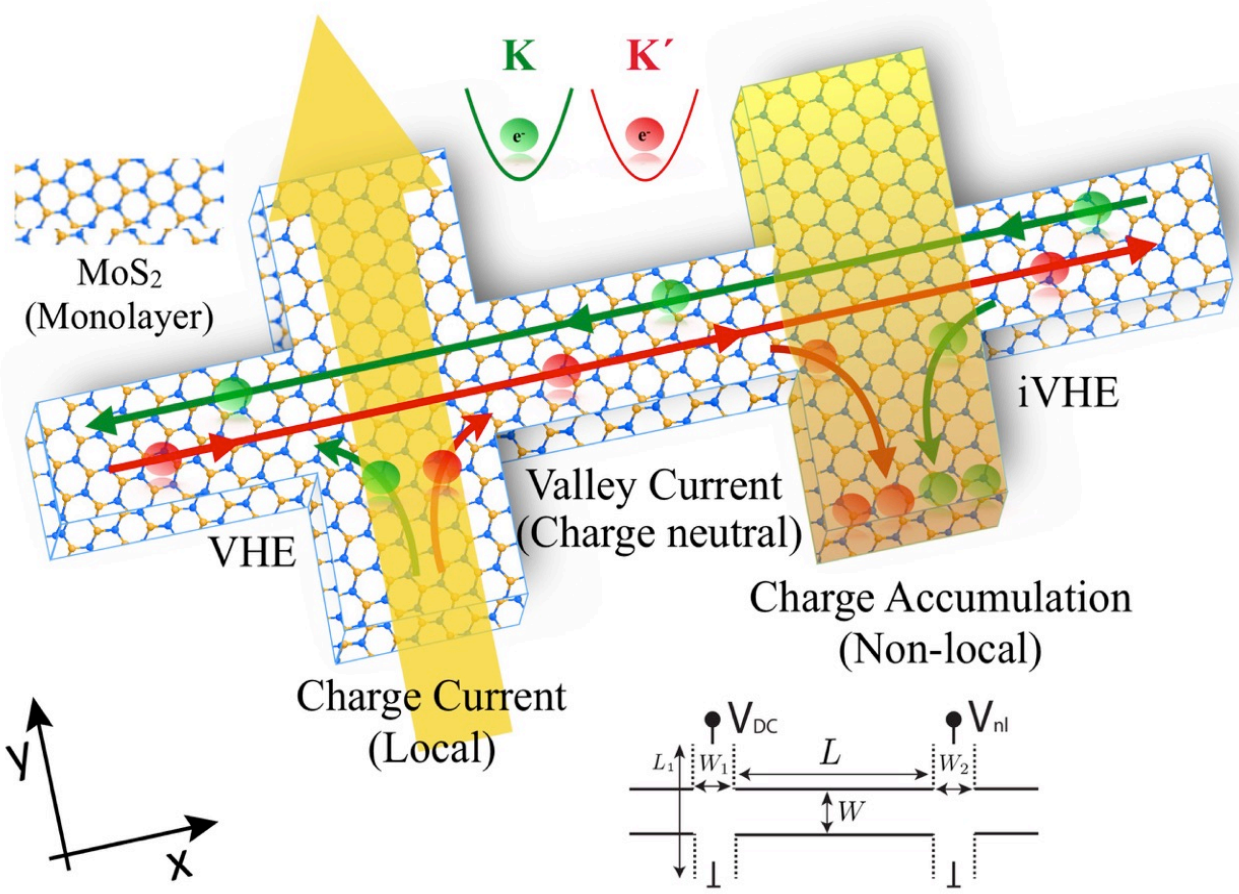
4-probe Measurements to Extract R_c and Sheet Resistance



Typical n-type characteristics are observed in MoS₂ FET devices

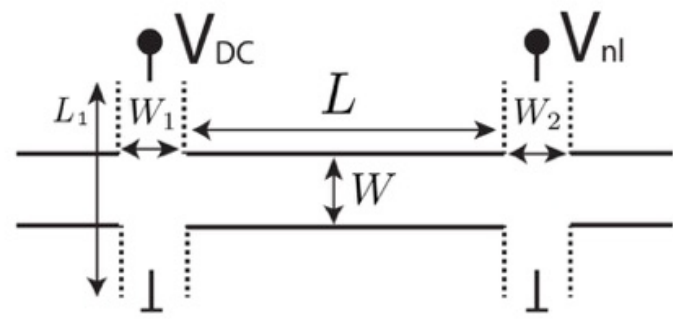
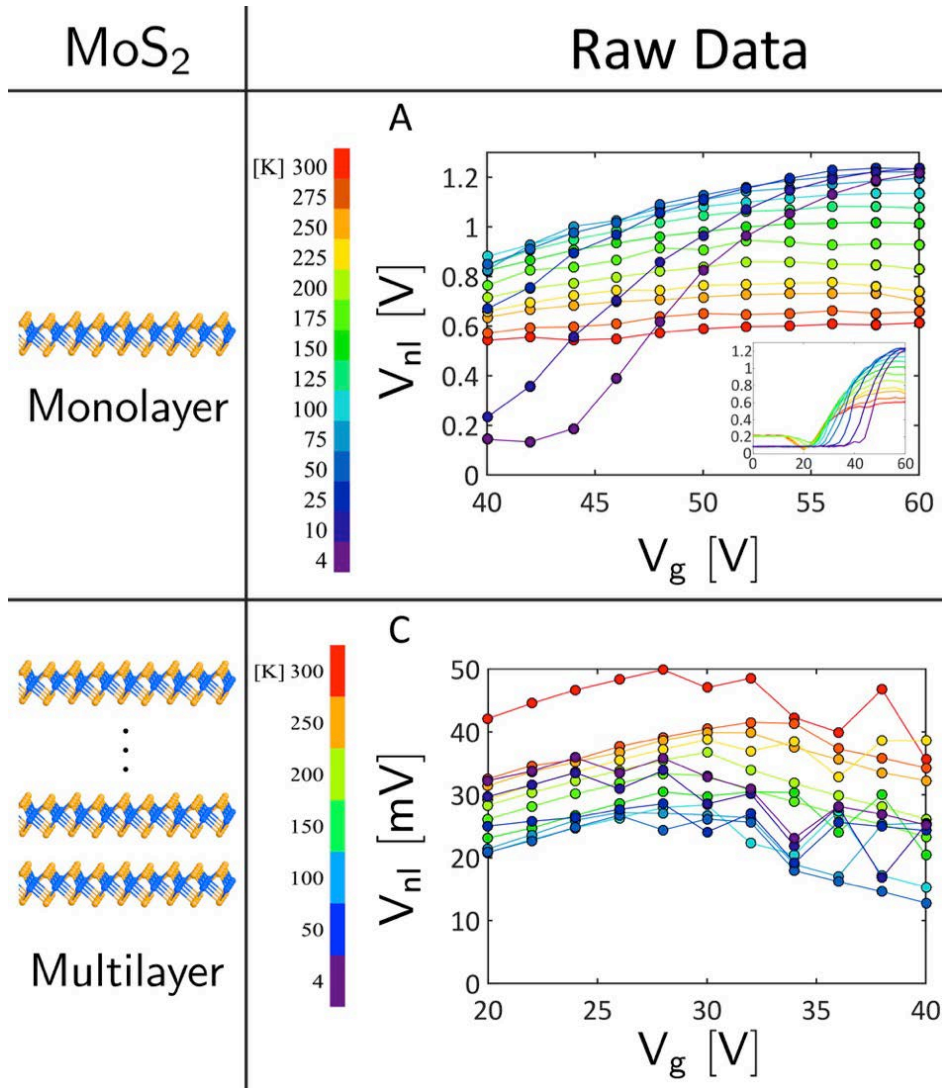
Non-local Measurement Set-up for Valley Current Detection

$L = 0.5\mu\text{m}$, $L_1 = 4.5\mu\text{m}$, $W_1 = 1\mu\text{m}$, $W = W_2 = 2\mu\text{m}$



T. Hung, et al., Science Advance, 5, eaau6478 (2019)

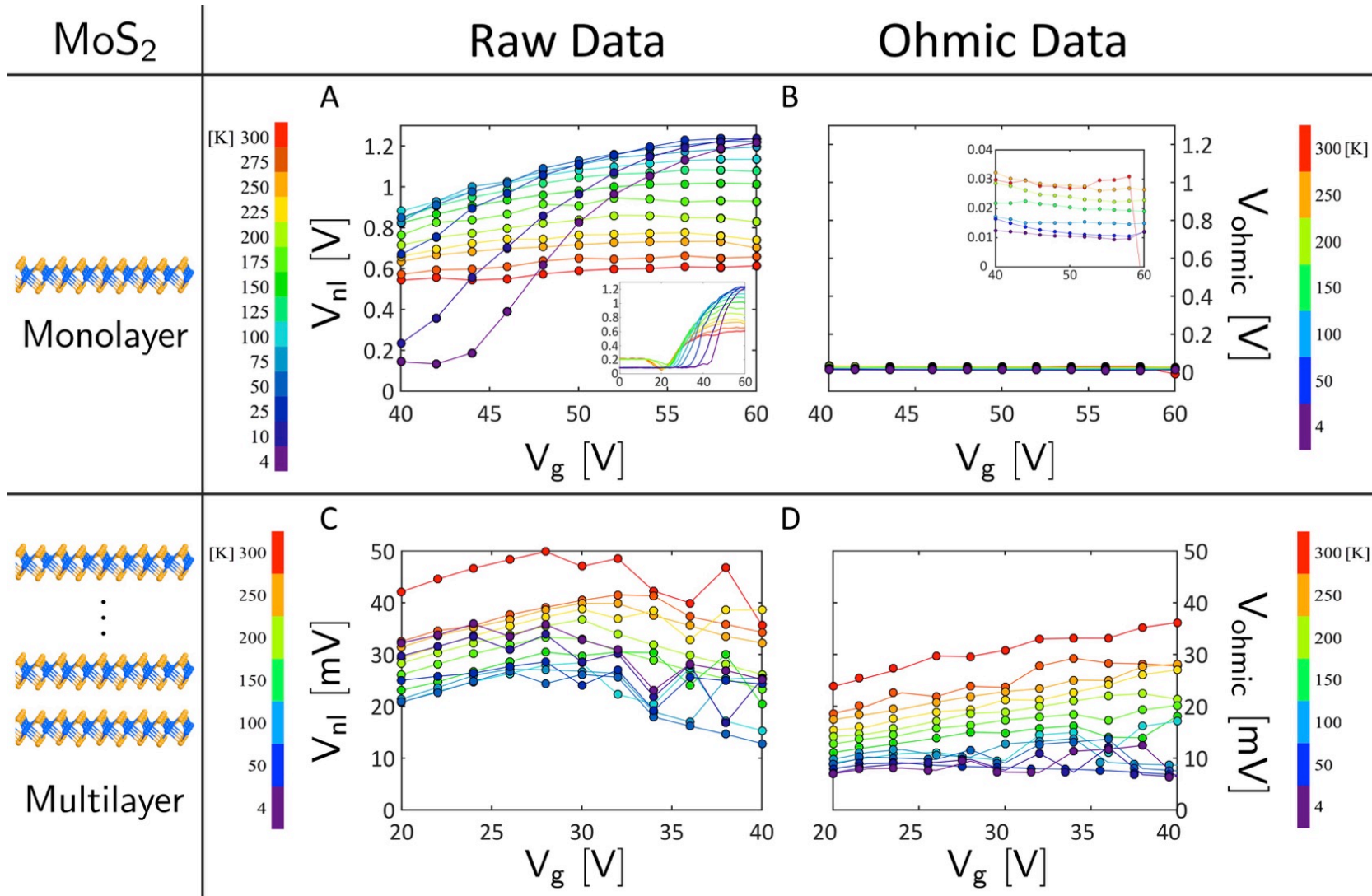
Non-local Measurements of Monolayer and Multi-layer MoS₂



$$V_{Ohmic} = I_{DC} \rho_{sh} \frac{W}{W_1} e^{-\frac{\pi L}{W}}$$

Large non-local Hall voltage measured in monolayer MoS₂

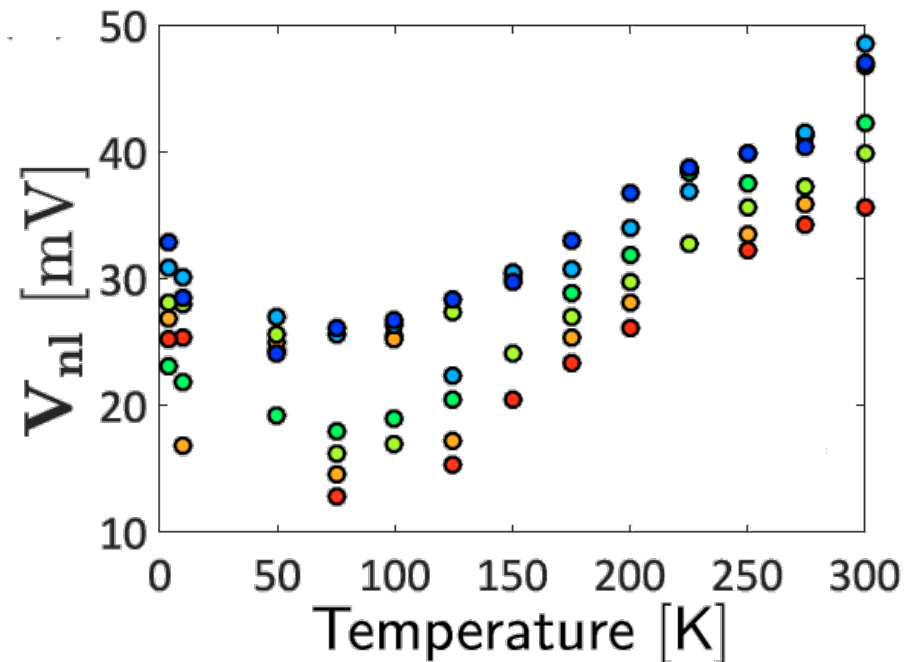
Non-local Measurements of Monolayer and Multi-layer MoS₂



Large non-local valley Hall voltage measured in monolayer MoS₂

Monolayer

Multi-layer



$$V_{Ohmic} = I_{DC} \rho_{sh} \frac{W}{W_1} e^{\frac{-\pi L}{W}}$$

Opposite temperature dependence trends are observed

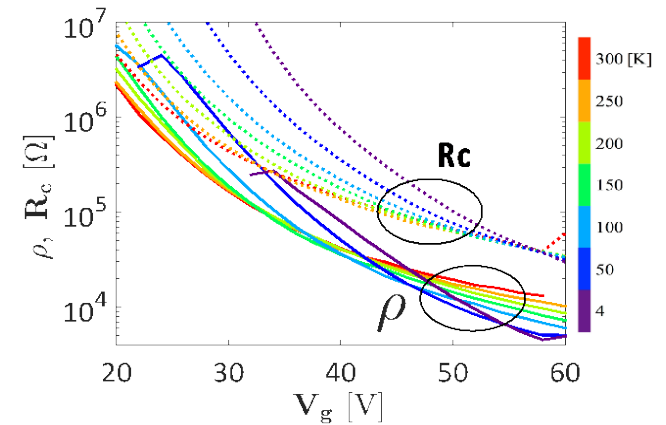
Monolayer

Multi-layer

$$V_{Ohmic}(T) = \frac{V_{ds}}{\left[2R_C(T) + \rho_{sh}(T) \frac{L_1}{W_1} \right]} \rho_{sh}(T) \frac{W}{W_1} e^{\frac{-\pi L}{W}}$$

Opposite temperature dependence trends are observed

Valley Hall Effect Induced Non-local Resistance



$$R_{nl}(T) \rightarrow R_{nl}(\rho(T), \lambda(T), \theta(T))$$

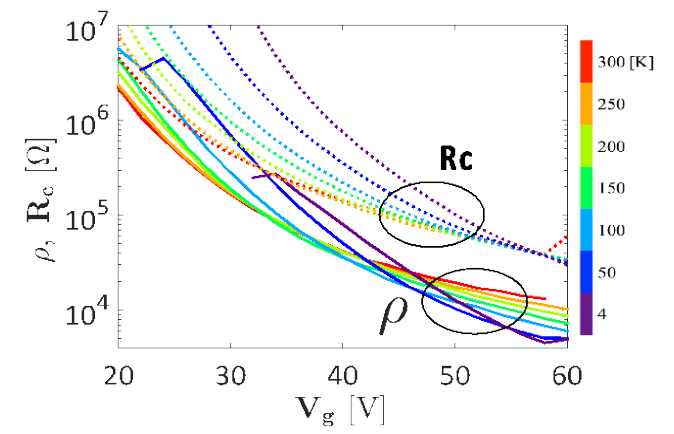
$$R_{nl} = \frac{V_{nl}}{I_{DC}} = \frac{2\rho\lambda W \sinh\left(\frac{W_1}{2\lambda}\right) \sinh\left(\frac{W_2}{2\lambda}\right) \theta^2 e^{-\frac{L}{\lambda}}}{\left(W_1 e^{\frac{W_1}{2\lambda}} + 2\lambda \sinh\left(\frac{W_1}{2\lambda}\right) \theta^2\right) \left(W_2 e^{\frac{W_2}{2\lambda}} + 2\lambda \sinh\left(\frac{W_2}{2\lambda}\right) \theta^2\right)}$$

$\theta^2 \ll 1$ ➔ $\frac{W_{1,2}}{\lambda} \ll 1$

$$R_{nl} = \frac{1}{2} \theta^2 \frac{W}{\sigma\lambda} e^{-\frac{L}{\lambda}}$$

Valley Hall Effect Induced Non-local Resistance

Experiment
Empirical



$$R_{nl}(T) \rightarrow R_{nl}(\rho(T), \lambda(T), \theta(T))$$

$$R_{nl} = \frac{V_{nl}}{I_{DC}} = \frac{2\rho\lambda W \sinh\left(\frac{W_1}{2\lambda}\right) \sinh\left(\frac{W_2}{2\lambda}\right) \theta^2 e^{-\frac{L}{\lambda}}}{\left(W_1 e^{\frac{W_1}{2\lambda}} + 2\lambda \sinh\left(\frac{W_1}{2\lambda}\right) \theta^2\right) \left(W_2 e^{\frac{W_2}{2\lambda}} + 2\lambda \sinh\left(\frac{W_2}{2\lambda}\right) \theta^2\right)}$$

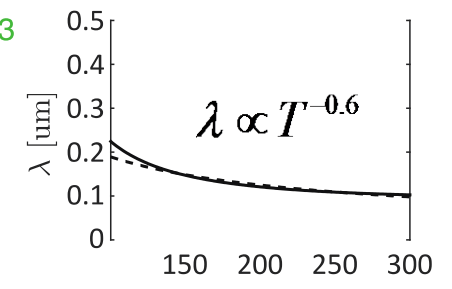
$\theta^2 \ll 1$
 $\frac{W_{1,2}}{\lambda} \ll 1$

$$R_{nl} = \frac{1}{2} \theta^2 \frac{W}{\sigma\lambda} e^{-\frac{L}{\lambda}}$$

Valley Hall Effect Induced Non-local Resistance

Experiment
Empirical

$$\lambda \propto T^{-0.73}$$



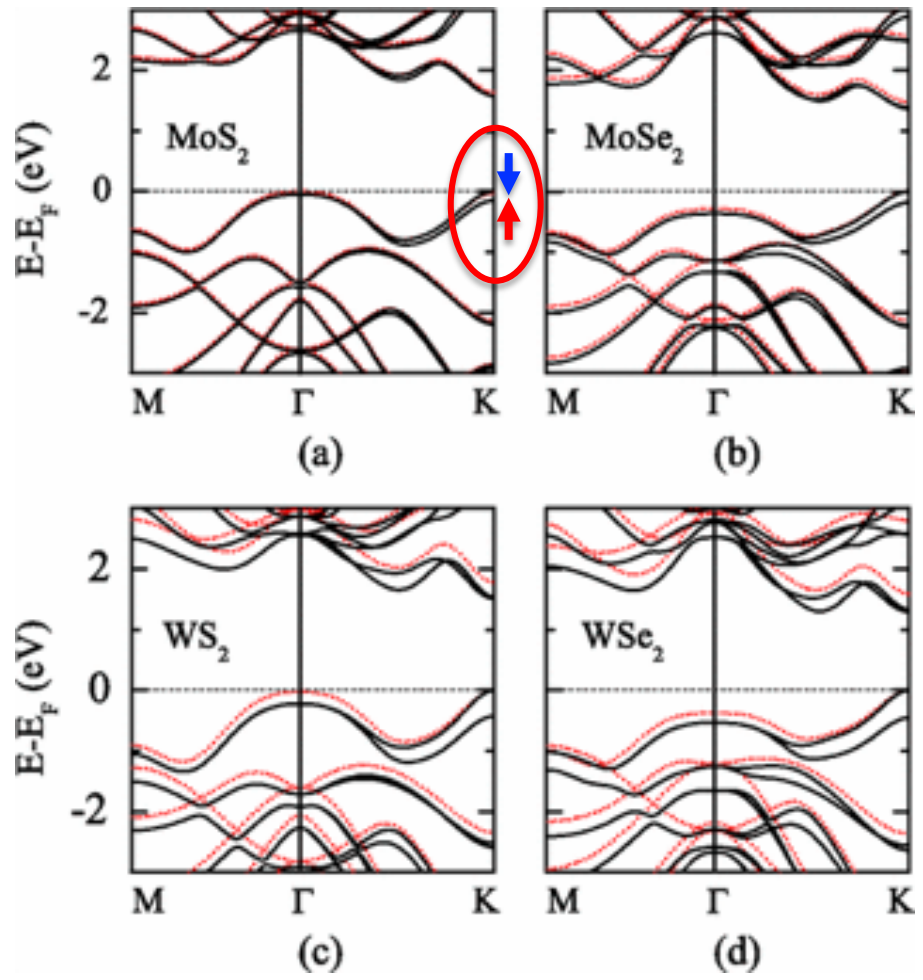
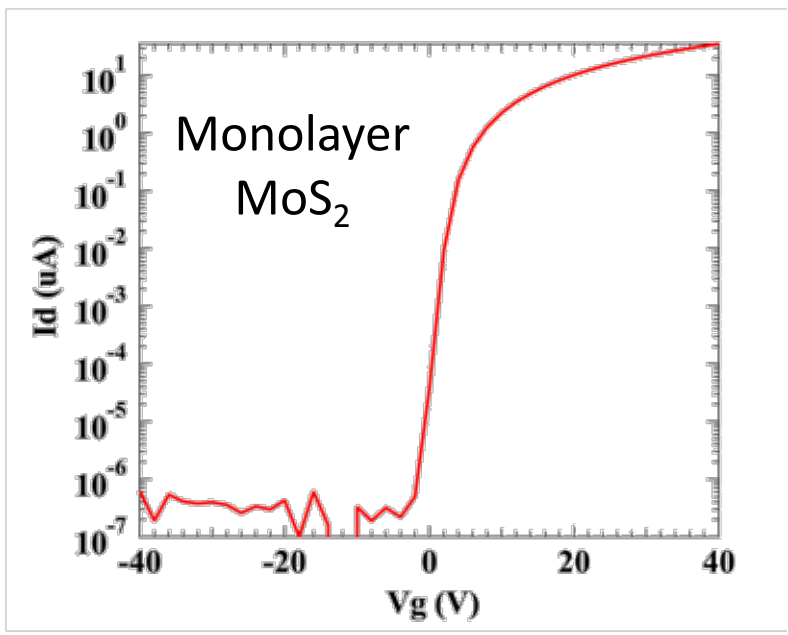
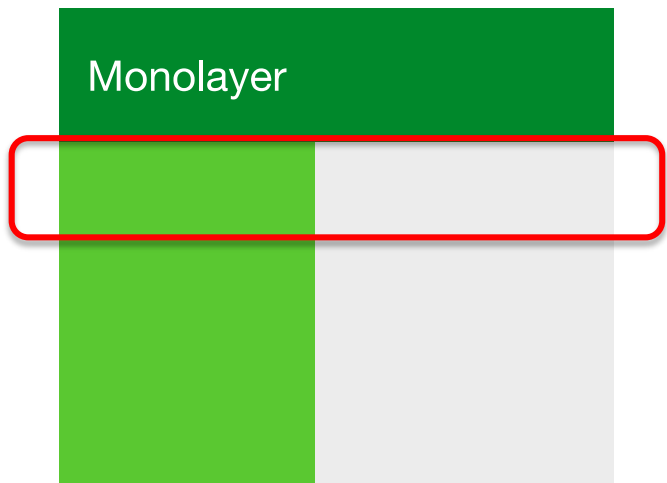
$$R_{nl} = \frac{V_{nl}}{I_{DC}} = \frac{2\rho\lambda W \sinh\left(\frac{W_1}{2\lambda}\right) \sinh\left(\frac{W_2}{2\lambda}\right) \theta^2 e^{-\frac{L}{\lambda}}}{\left(W_1 e^{\frac{W_1}{2\lambda}} + 2\lambda \sinh\left(\frac{W_1}{2\lambda}\right) \theta^2\right) \left(W_2 e^{\frac{W_2}{2\lambda}} + 2\lambda \sinh\left(\frac{W_2}{2\lambda}\right) \theta^2\right)}$$

$\theta^2 \ll 1$

 $\frac{W_{1,2}}{\lambda} \ll 1$

$$R_{nl} = \frac{1}{2} \theta^2 \frac{W}{\sigma\lambda} e^{-\frac{L}{\lambda}}$$

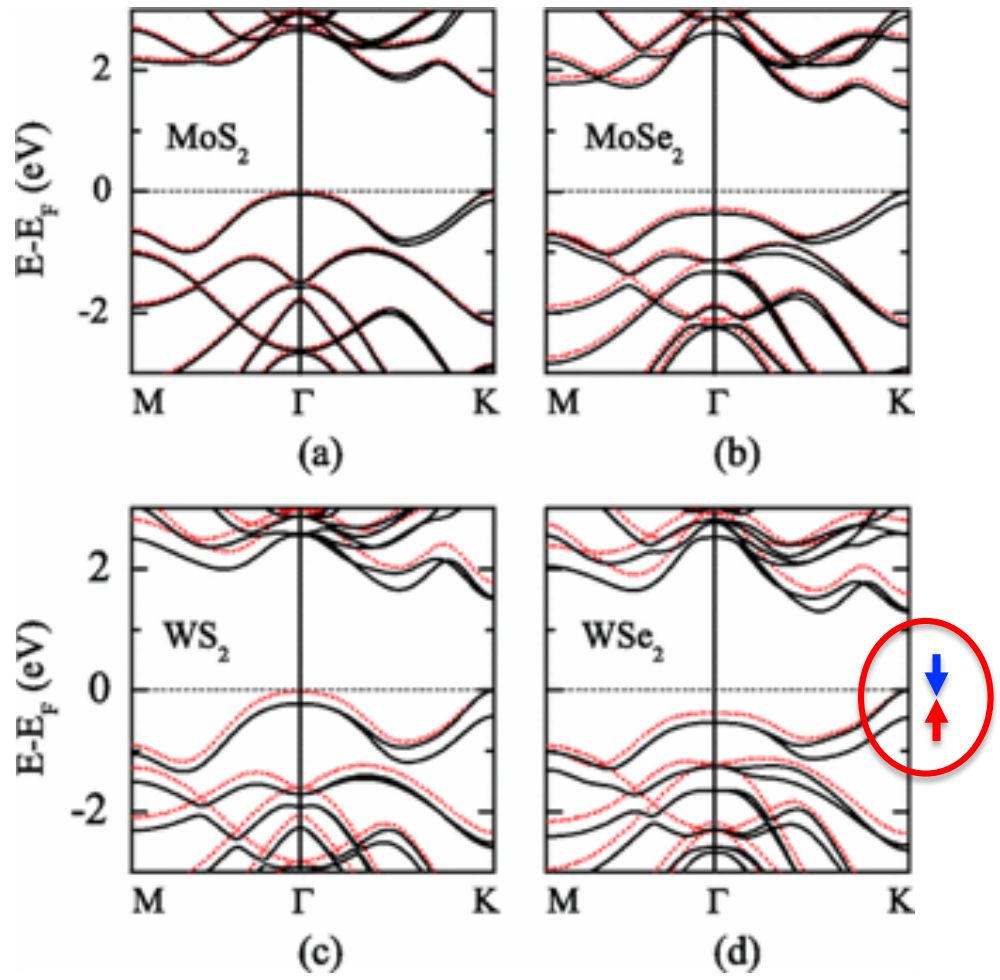
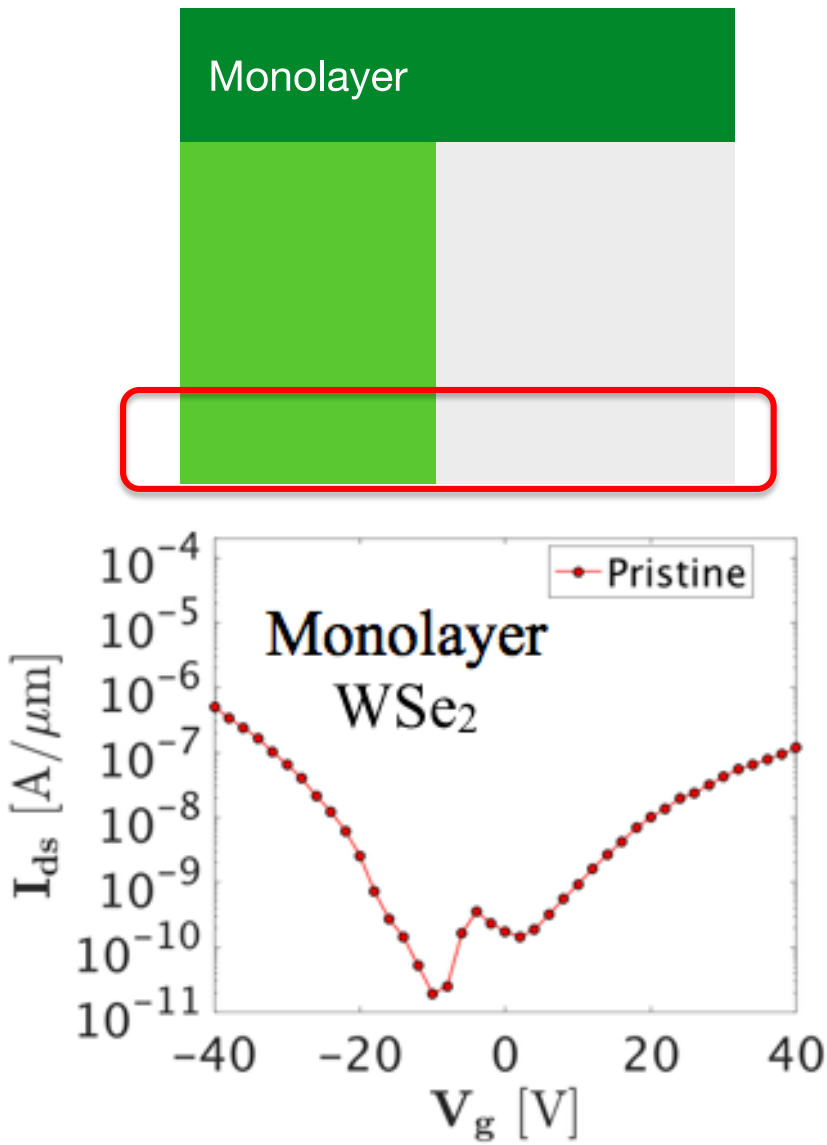
Large Spin Splitting in WSe₂ Valence Band



Z. Y. Zhu, et al., PRB **84**, 153402 (2011)

Need to access p-branch, hole carriers

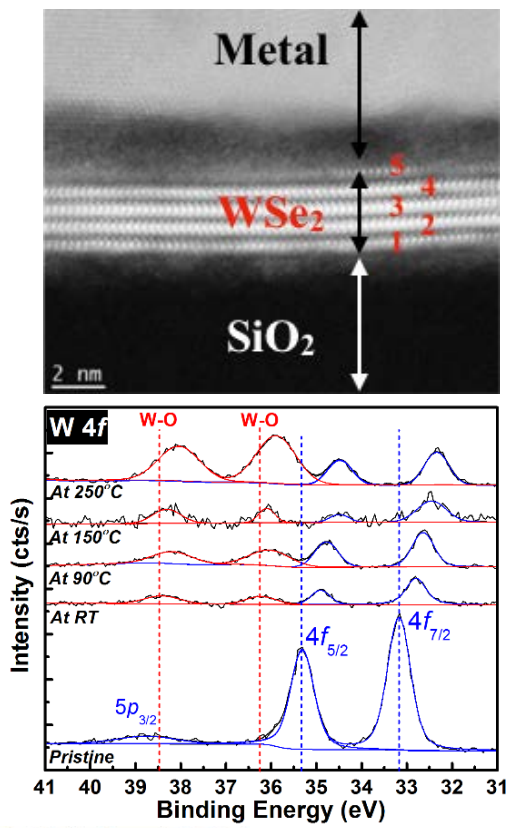
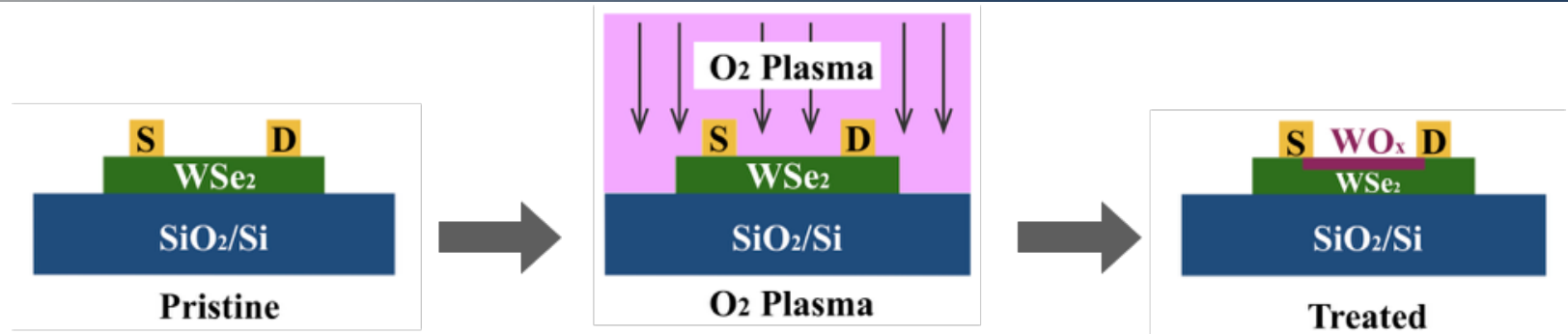
Large Spin Splitting in WSe₂ Valence Band



Z. Y. Zhu, et al., PRB **84**, 153402 (2011)

Although p-branch is present, the on-state current needs to be improved!

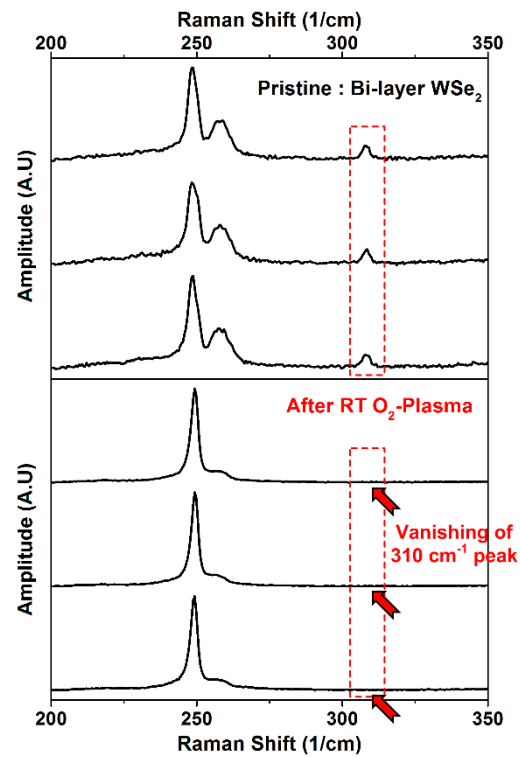
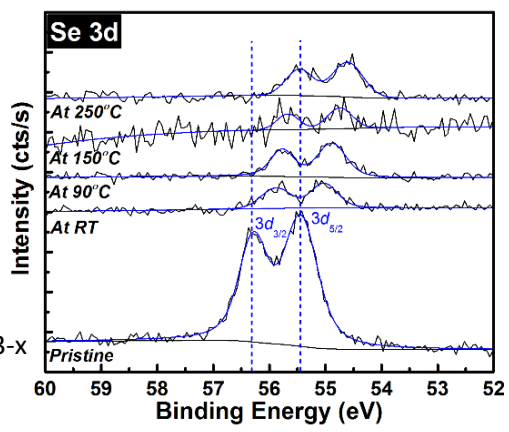
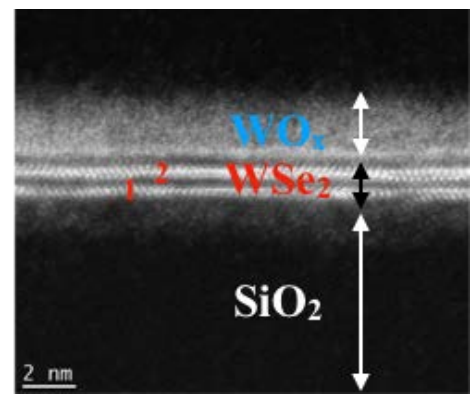
Air Stable P-type Doping for WSe₂ FETs



250°C
5L → 2L

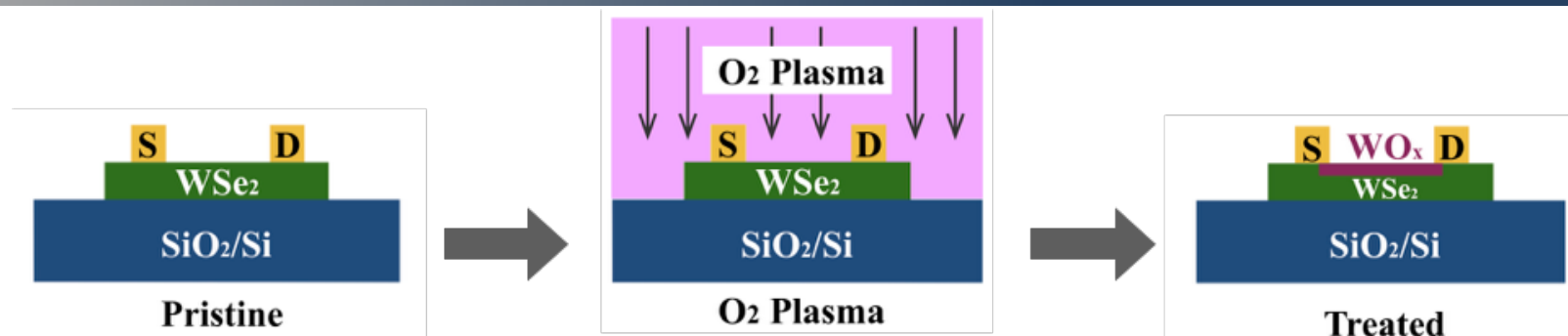
Temp
Fewer

WSe₂ → WO_{3-x}



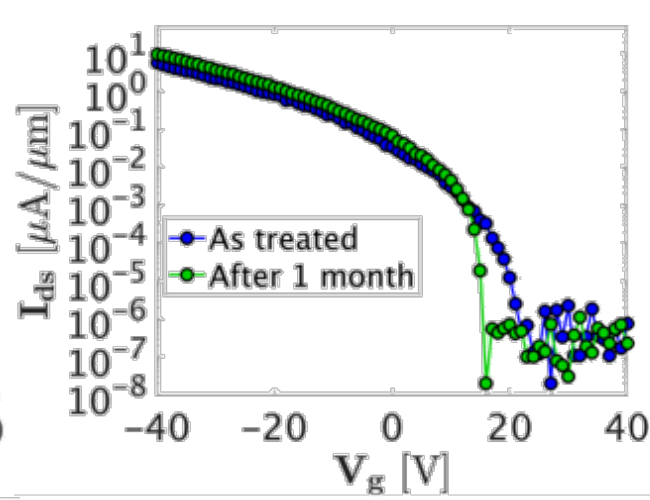
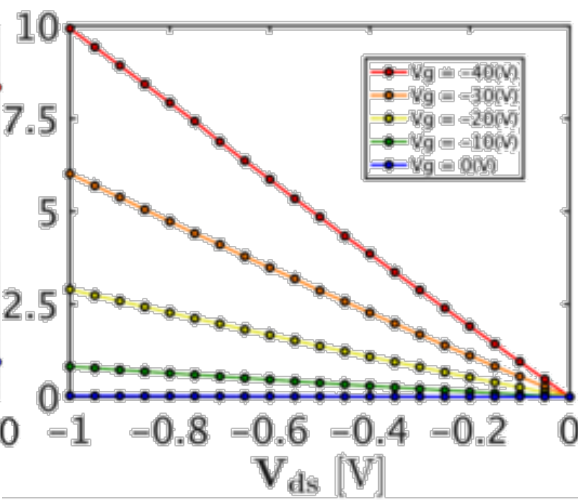
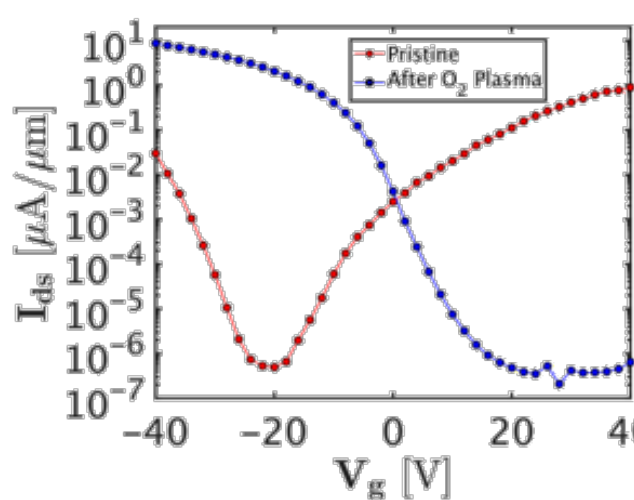
RT Bilayer → Monolayer

Air Stable P-type Doping for WSe₂ FETs



Tunable P-type Doping

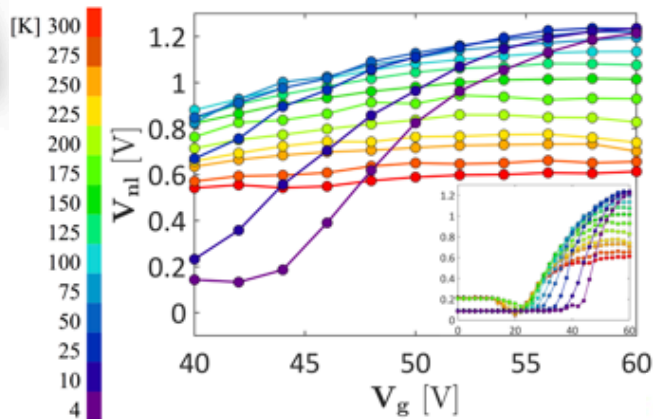
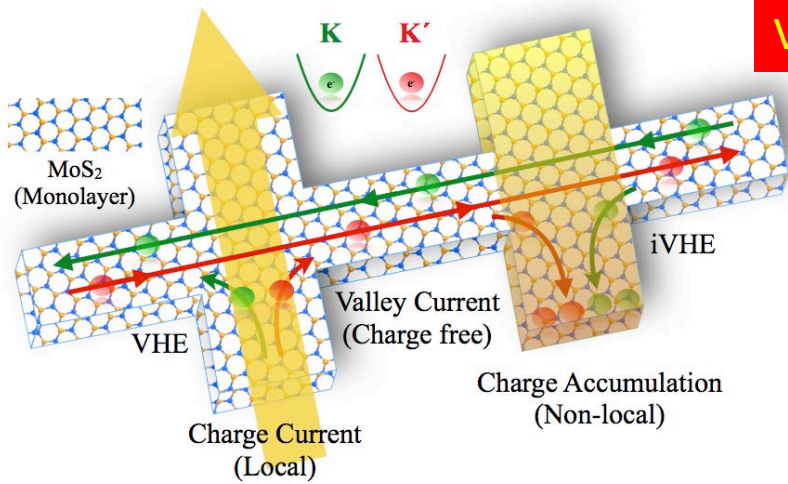
Air Stable



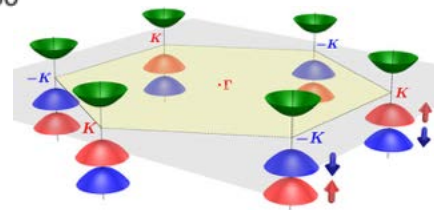
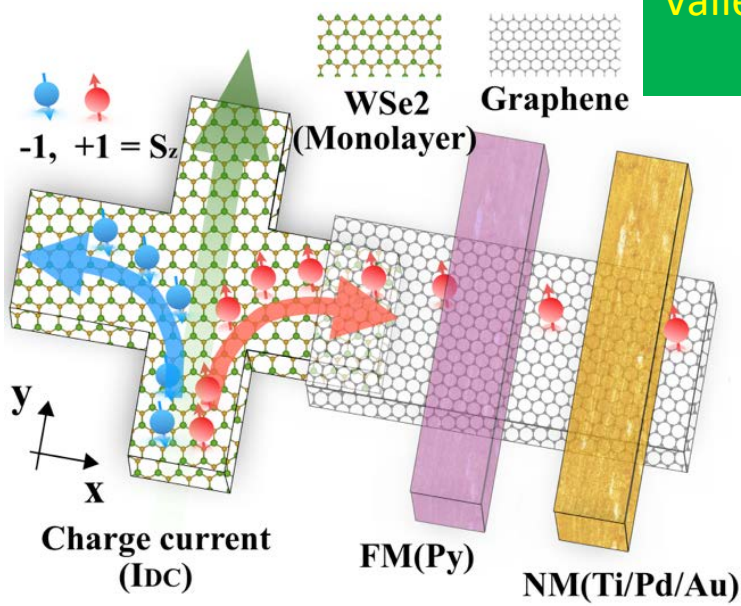
T. Hung, C.-S. Pang, et. al., submitted (2019)

Electrical Detection of Valley Coupled Spin Currents in WSe_2

Valley Current Detection Only in MoS_2

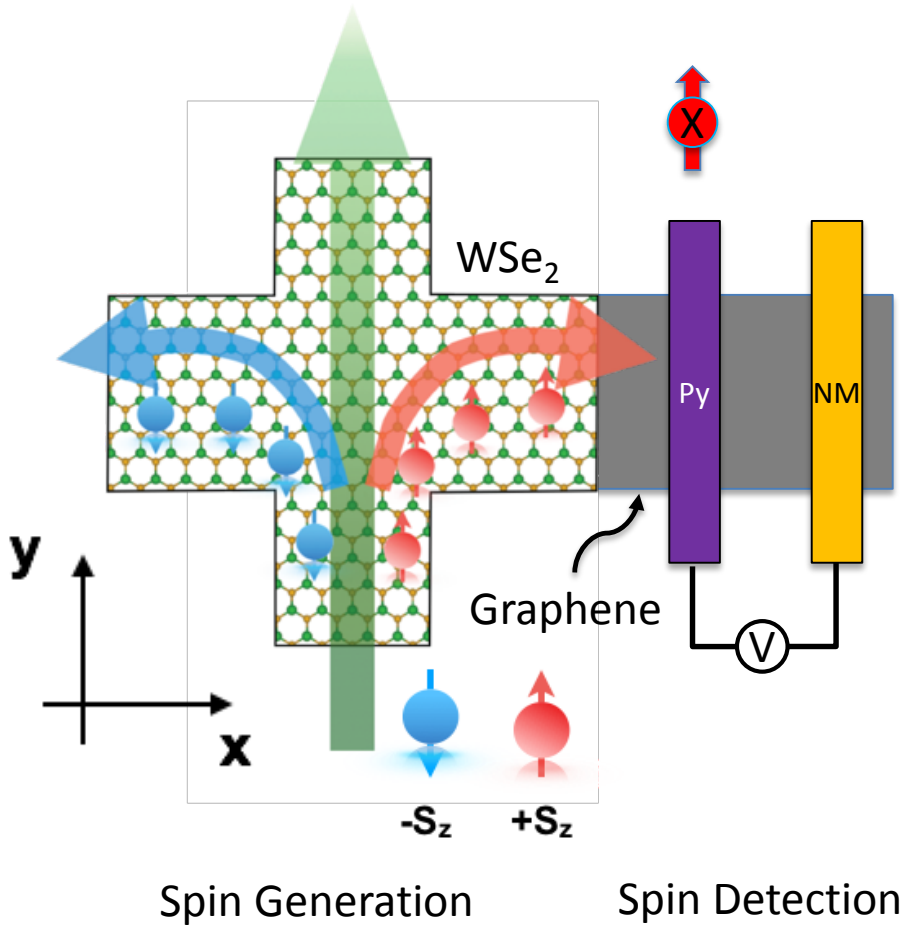


Valley Coupled Spin Current Detection in WSe_2

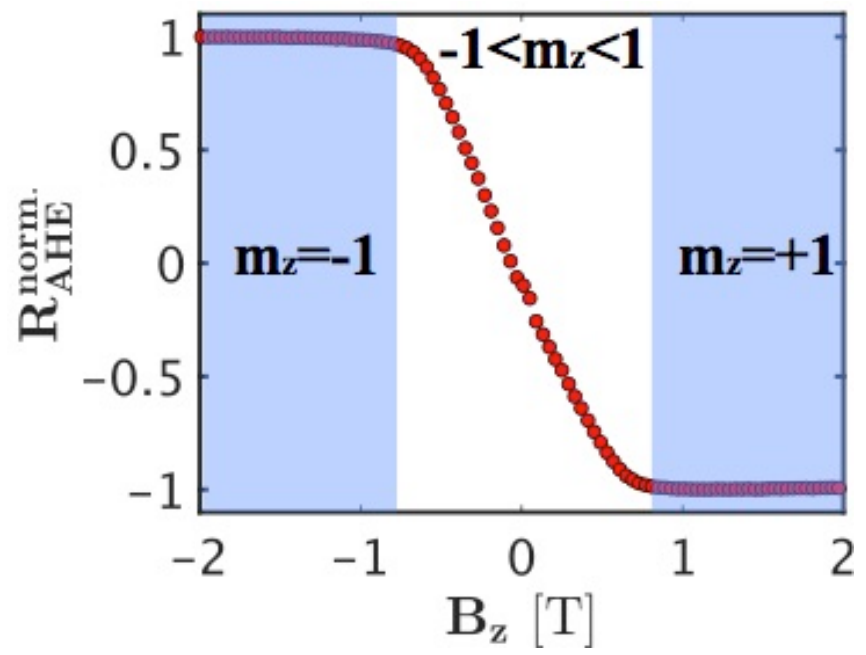
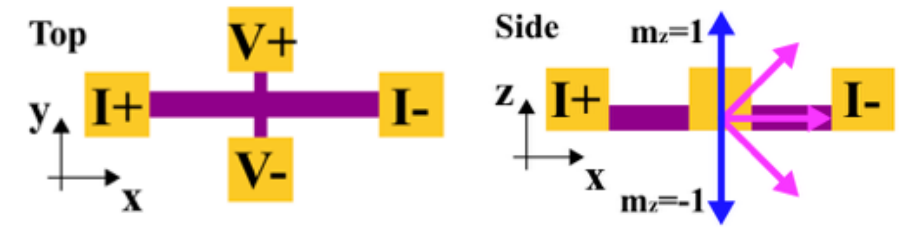


- Ferromagnetic (FM) contact for spin detection
- Graphene channel for spin diffusion
- Nonlocal spin valve device configuration
- Magnetic field scanning to align FM from in-plane to out-of-plane magnetization

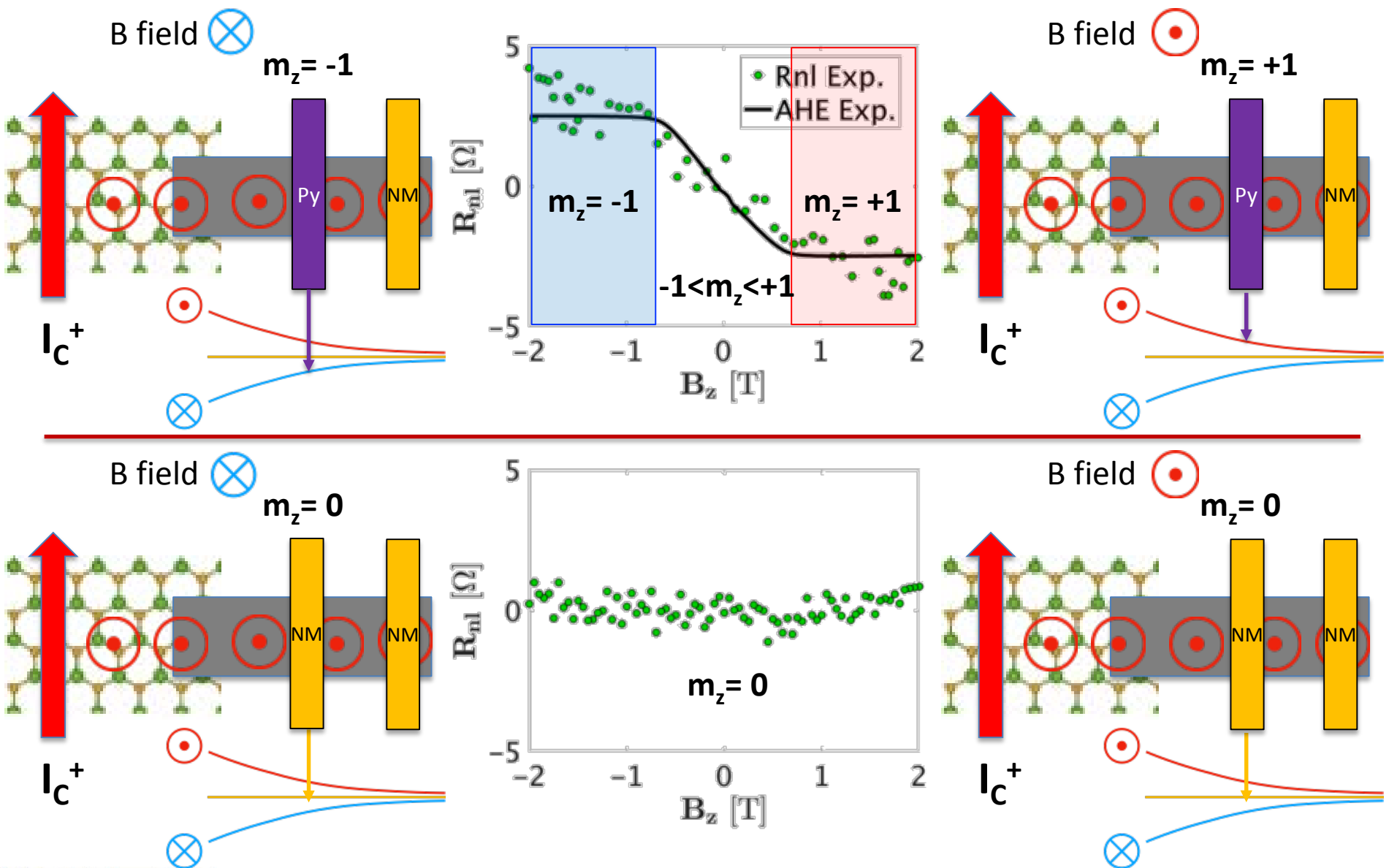
Nonlocal Spin Valve Measurements for Out-of-Plane Spins



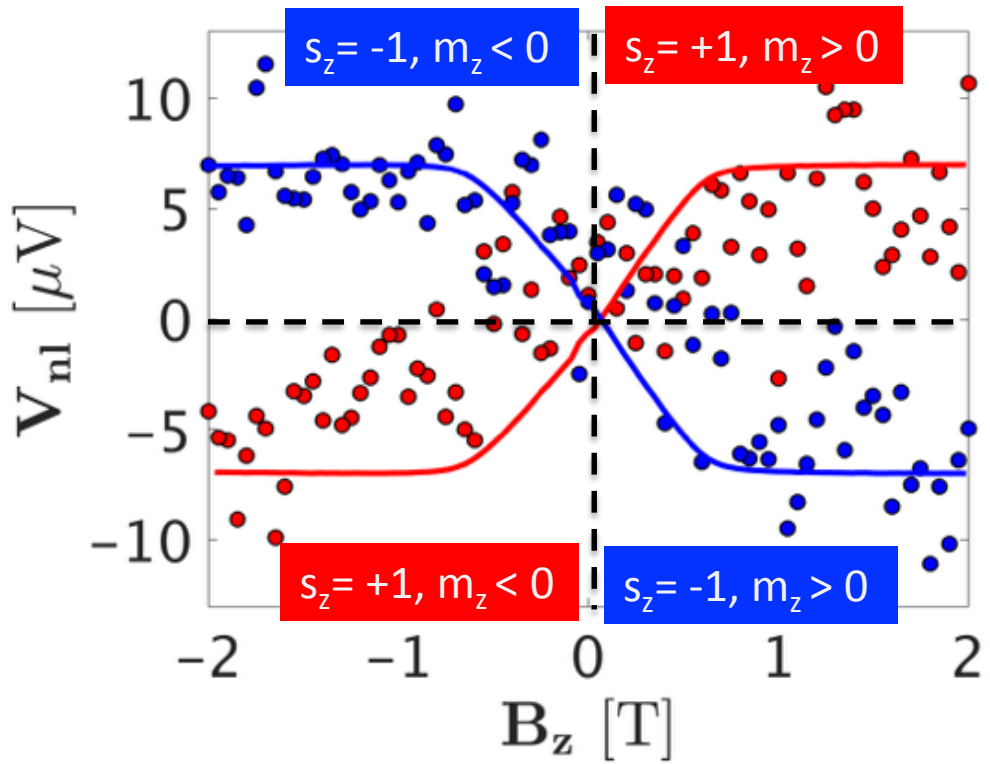
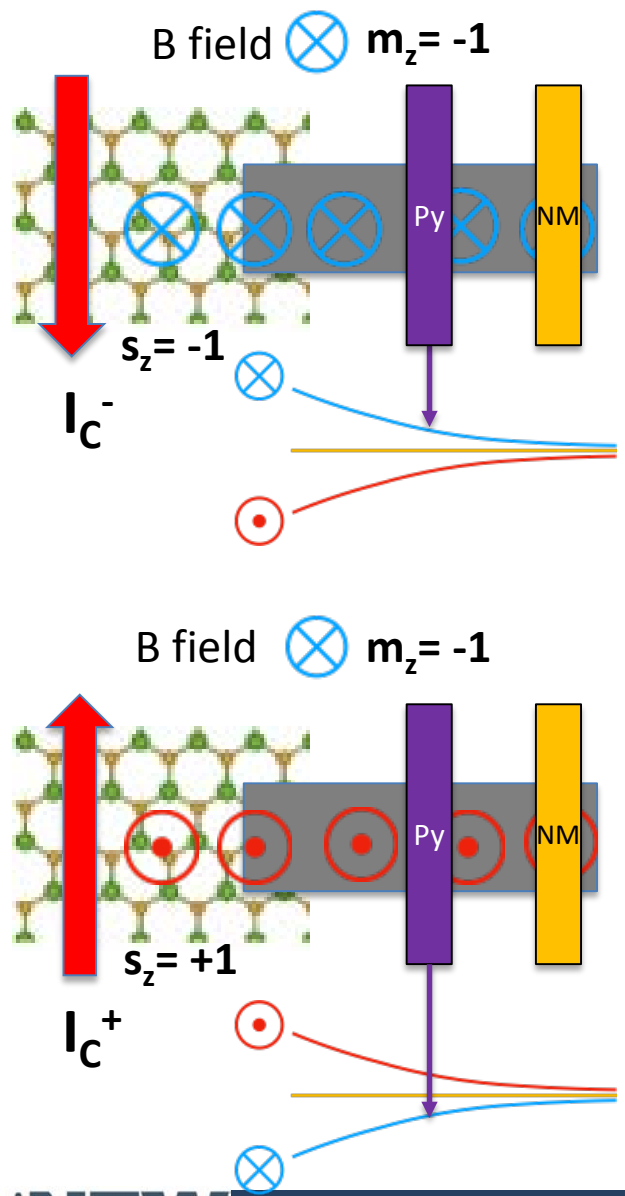
In-plane FM - Py's
Anomalous Hall Effect



Nonlocal Spin Valve Measurements for Out-of-Plane Spins



Nonlocal Spin Valve Measurements for Out-of-Plane Spins



Collaborators:

Prof. Moon Kim's group (UT Dallas)

Prof. Robert Wallace's group (UT Dallas)



<http://www.purdue.edu/discoverypark/newlimits/index.php>

Thank you!